

## FDB8860

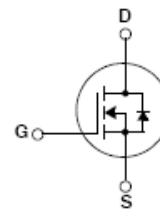
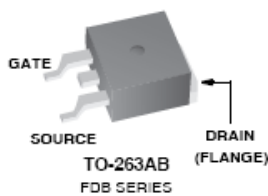
### N-Channel Logic Level PowerTrench® MOSFET 30V, 80A, 2.6mΩ

#### Features

- $R_{DS(ON)} = 1.9m\Omega$  (Typ),  $V_{GS} = 5V$ ,  $I_D = 80A$
- $Q_{g(5)} = 89nC$  (Typ),  $V_{GS} = 5V$
- Low Miller Charge
- Low  $Q_{RR}$  Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

#### Applications

- 12V Automotive Load Control
- Start / Alternator Systems
- Electronic Power Steering Systems
- ABS
- DC-DC Converters



## MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current Continuous ( $V_{GS} = 10\text{V}$ , $T_C < 163^\circ\text{C}$ )	80	A
	Continuous ( $V_{GS} = 5\text{V}$ , $T_C < 162^\circ\text{C}$ )	80	A
	Continuous ( $V_{GS} = 10\text{V}$ , $T_C = 25^\circ\text{C}$ , with $R_{\theta JA} = 43^\circ\text{C/W}$ )	31	A
	Pulsed	Figure 4	A
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	947	mJ
$P_D$	Power Dissipation	254	W
	Derate above $25^\circ\text{C}$	1.7	$\text{W}/^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

## Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case	0.59	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (Note 2)	62	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-263, $1\text{in}^2$ copper pad area	43	$^\circ\text{C/W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB8860	FDB8860	TO-263AB	330mm	24mm	800units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 1\text{mA}$ , $V_{GS} = 0\text{V}$	30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}$ $V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	1	1.7	3	V
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}$ , $V_{GS} = 10\text{V}$	-	1.6	2.3	m $\Omega$
		$I_D = 80\text{A}$ , $V_{GS} = 5\text{V}$	-	1.9	2.6	
		$I_D = 80\text{A}$ , $V_{GS} = 4.5\text{V}$	-	2.1	2.7	
		$I_D = 80\text{A}$ , $V_{GS} = 10\text{V}$ , $T_J = 175^\circ\text{C}$	-	2.5	3.6	

### Dynamic Characteristics

$C_{ISS}$	Input Capacitance	$V_{DS} = 15\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	9460	12585	pF	
$C_{OSS}$	Output Capacitance		-	1710	2275	pF	
$C_{RSS}$	Reverse Transfer Capacitance		-	1050	1575	pF	
$R_G$	Gate Resistance	$f = 1\text{MHz}$	-	1.8	-	$\Omega$	
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 15\text{V}$ $I_D = 80\text{A}$ $I_g = 1.0\text{mA}$	-	165	214	nC
$Q_{g(5)}$	Total Gate Charge at 5V	$V_{GS} = 0\text{V}$ to 5V		-	89	115	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V}$ to 1V		-	9.1	12	nC
$Q_{gs}$	Gate to Source Gate Charge			-	26	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau			-	18	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	33	-	nC

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Switching Characteristics**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{(on)}$	Turn-On Time	$V_{DD} = 15\text{V}, I_D = 80\text{A}$ $V_{GS} = 5\text{V}, R_{GS} = 1\Omega$	-	-	340	ns
$t_{d(on)}$	Turn-On Delay Time		-	14	-	ns
$t_r$	Turn-On Rise Time		-	213	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	79	-	ns
$t_f$	Turn-Off Fall Time		-	49	-	ns
$t_{off}$	Turn-Off Time		-	-	192	ns

**Drain-Source Diode Characteristics**

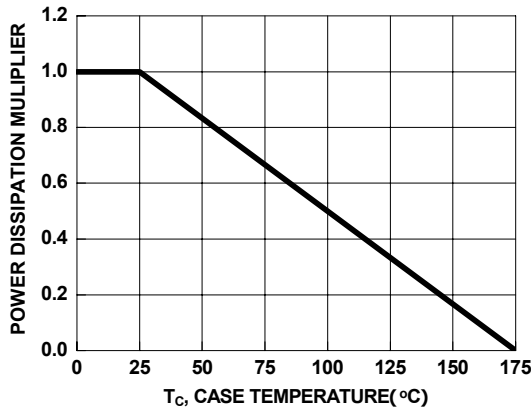
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{SD}$	Source to Drain Diode Voltage	$I_{SD} = 80\text{A}$	-	-	1.25	V
		$I_{SD} = 40\text{A}$	-	-	1.0	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 80\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	43	ns
$Q_{rr}$	Reverse Recovery Charge	$I_{SD} = 80\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	29	nC

**Notes:**

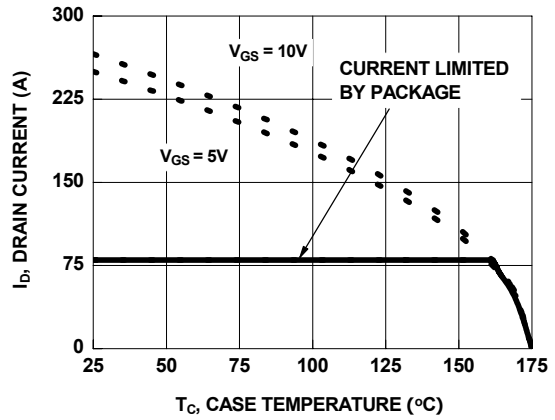
- 1: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.47\text{mH}$ ,  $I_{AS} = 64\text{A}$ ,  $V_{DD} = 30\text{V}$ ,  $V_{GS} = 10\text{V}$ .
- 2: Pulse width = 100s

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>  
 All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

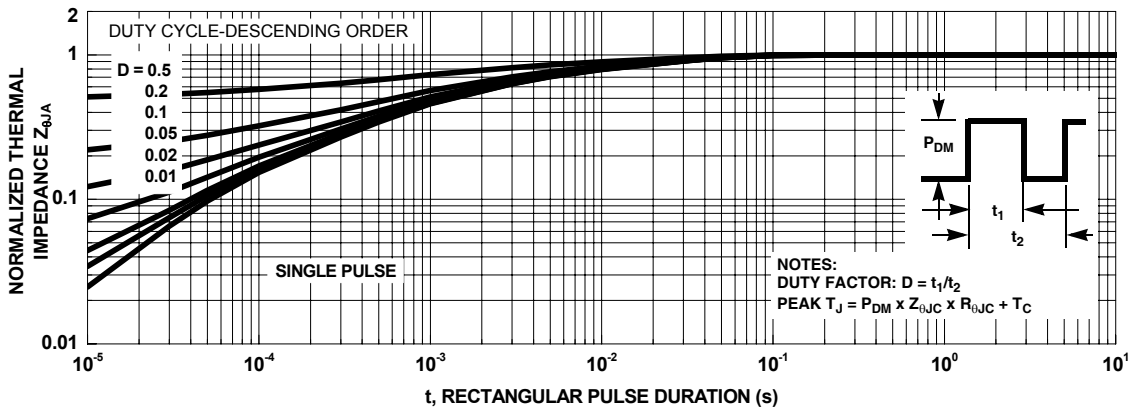
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



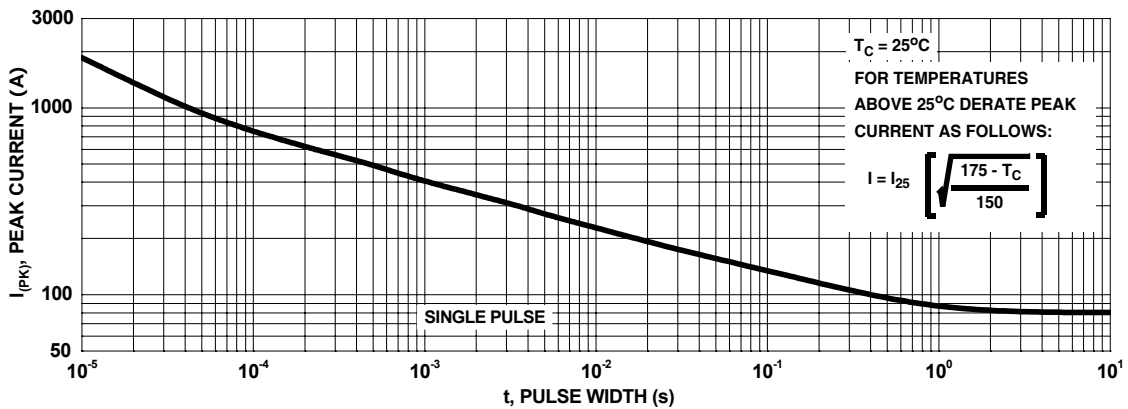
**Figure 1. Normalized Power Dissipation vs Case Temperature**



**Figure 2. Maximum Continuous Drain Current vs Case Temperature**

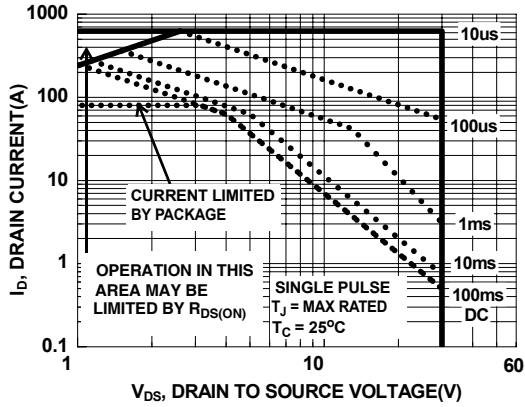


**Figure 3. Normalized Maximum Transient Thermal Impedance**

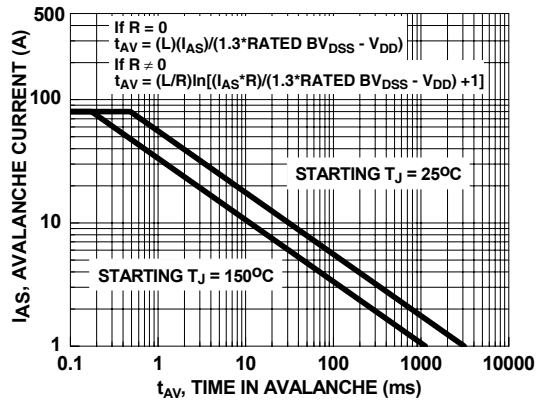


**Figure 4. Peak Current Capability**

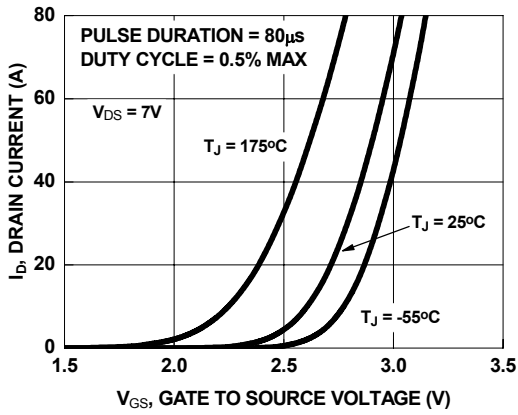
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



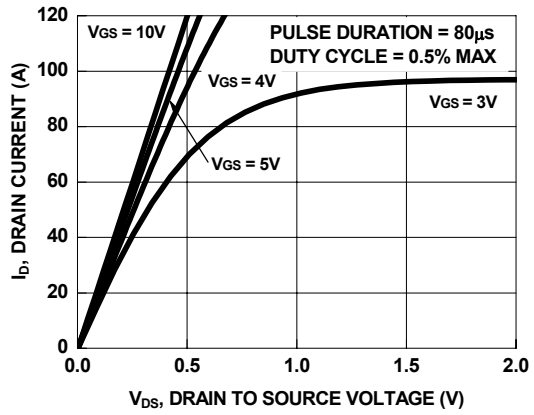
**Figure 5. Forward Bias Safe Operating Area**



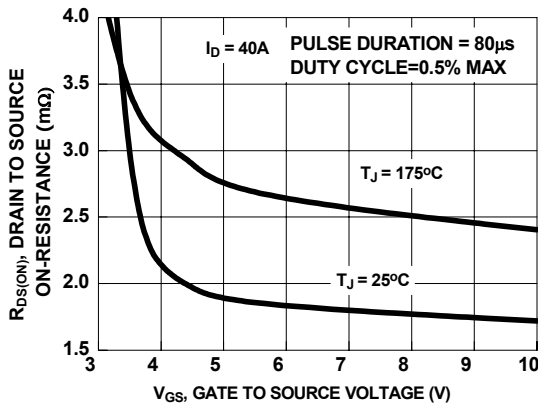
NOTE: Refer to Fairchild Application Notes AN7514 and AN7515  
**Figure 6. Unclamped Inductive Switching Capability**



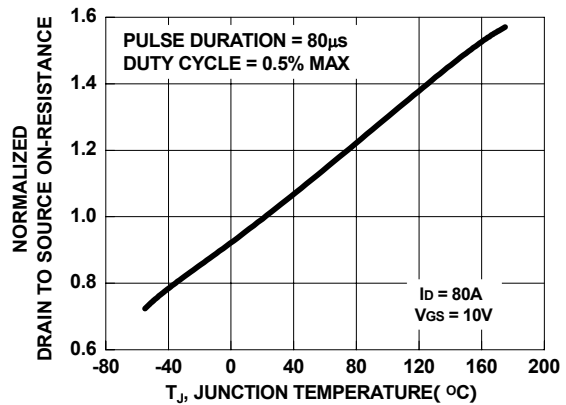
**Figure 7. Transfer Characteristics**



**Figure 8. Saturation Characteristics**

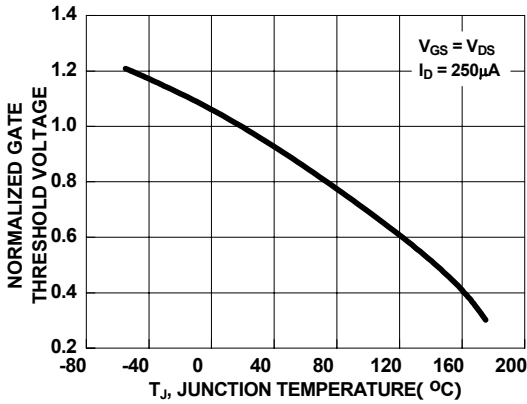


**Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage**

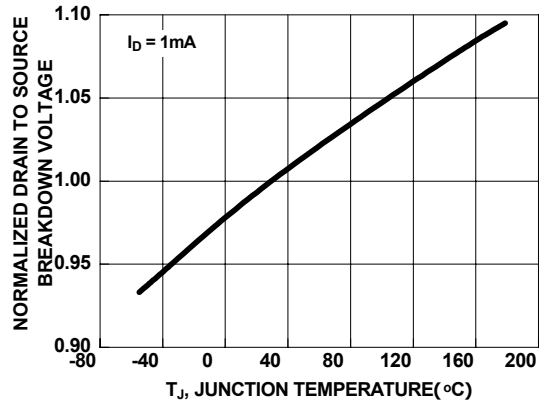


**Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature**

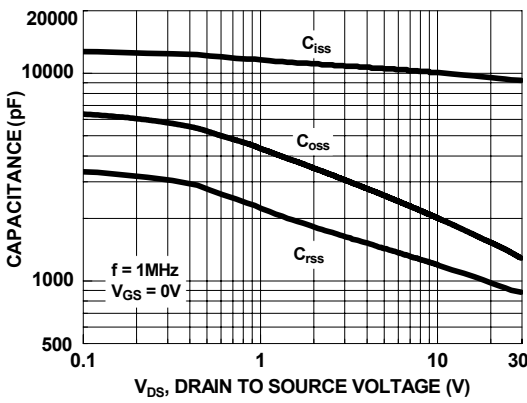
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



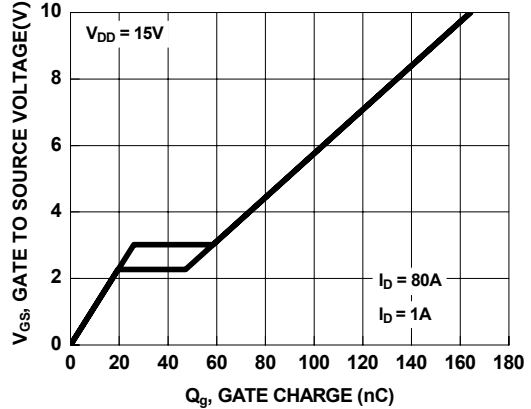
**Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature**



**Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature**



**Figure 13. Capacitance vs Drain to Source Voltage**



**Figure 14. Gate Charge vs Gate to Source Voltage**

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